GENERAL DESCRIPTION

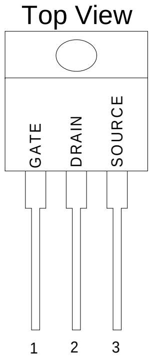
This high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

FEATURES

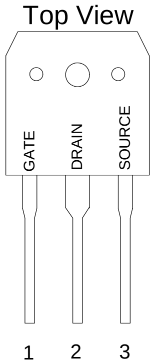
- Robust High Voltage Termination
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and V_{DS}(on) Specified at Elevated Temperature
- Isolated Mounting Hole Reduces Mounting Hardware

PIN CONFIGURATION

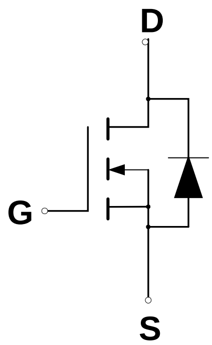
TO-220F
Top View



TO-3P/T-O247
Top View



SYMBOL



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain to Current — Continuous (TO3P)	I_D	14	A
— Pulsed	I_{DM}	42	
Gate-to-Source Voltage — Continue	V_{GS}	±30	V
Total Power Dissipation – TO220FP	P_D	47	W
– TO3P		245	W/℃
– TO247		201	
Derate above 25℃ – TO220FP		0.37	
– TO3P		2.1	
– TO247		1.9	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	℃
Single Pulse Drain-to-Source Avalanche Energy — T_J = 25℃ (V_{DD} = 100V, V_{GS} = 10V, I_L = 12A, L = 10mH, R_G = 25Ω)	E_{AS}	720	mJ
Thermal Resistance — Junction to Case -TO220FP	θ_{JC}	3.15	℃/W
— TO3P		0.47	
— Junction to Ambient -TO220FP	θ_{JA}	62.5	
— TO3P		40	
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	℃
ESD SENSITIVITY — HBM, C=100pF, R=1.5kΩ	Vesd	2000	V

ORDERING INFORMATION

Part Number	Package
GPT14N65GN3P*	TO-3P
GPT14N65GN247*	TO-247
GPT14N65DGN220FP*	TO-220F

***Note:** G : Suffix for PB Free Product

ELECTRICAL CHARACTERISTICS

Unless otherwise specified, T_J = 25℃.

Characteristic		Symbol	GPT14N65 Min	GPT14N65 Typ	GPT14N65 Max	Units
Drain-Source Breakdown Voltage (V_{GS} = 0 V, I_D = 250 μA)		$V_{(BR)DSS}$	650			V
Drain-Source Leakage Current (V_{DS} = 650 V, V_{GS} = 0 V)		I_{DSS}			1	uA
Gate-Source Leakage Current-Forward (V_{gsf} = 30 V, V_{DS} = 0 V)		I_{GSSF}			100	nA
Gate-Source Leakage Current-Reverse (V_{gsr} = 30 V, V_{DS} = 0 V)		I_{GSSR}			100	nA
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)		$V_{GS(th)}$	3		5	V
Static Drain-Source On-Resistance (V_{GS} = 10 V, I_D = 7 A) *		$R_{DS(on)}$			0.5	Ω
Forward Transconductance (V_{DS} = 50 V, I_D = 7 A) *		g_{FS}		14		S
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz)	C_{iss}		2861		pF
Output Capacitance		C_{oss}		235		pF
Reverse Transfer Capacitance		C_{rss}		10.4		pF
Turn-On Delay Time	(V_{DD} = 325 V, I_D = 14 A, R_G = 25Ω) *	$t_{d(on)}$		40.5		ns
Rise Time		t_r		77.8		ns
Turn-Off Delay Time		$t_{d(off)}$		62.4		ns
Fall Time		t_f		38.9		ns
Total Gate Charge	(V_{DS} = 520 V, I_D = 14 A, V_{GS} = 10 V)*	Q_g		56.1		nC
Gate-Source Charge		Q_{gs}		17.8		nC
Gate-Drain Charge		Q_{gd}		22.7		nC
SOURCE-DRAIN DIODE CHARACTERISTICS						
Forward On-Voltage(1)	(I_S = 14 A, d_{IS}/d_t = 100A/μs)	V_{SD}			1.5	V
Forward Turn-On Time		t_{on}		**		ns
Reverse Recovery Time		t_{rr}		509.3		ns

* Pulse Test: Pulse Width ≦300μs, Duty Cycle ≦2%

** Negligible, Dominated by circuit inductance

TYPICAL ELECTRICAL CHARACTERISTICS

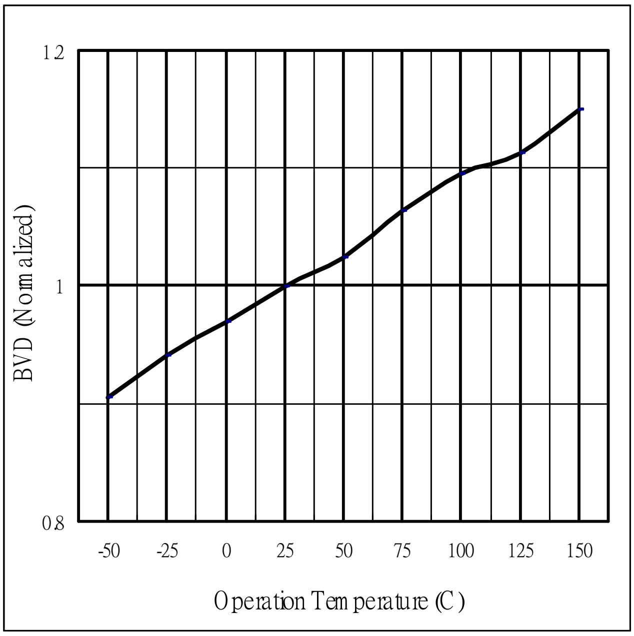


Fig 1. On-Resistance Vs. Temperature

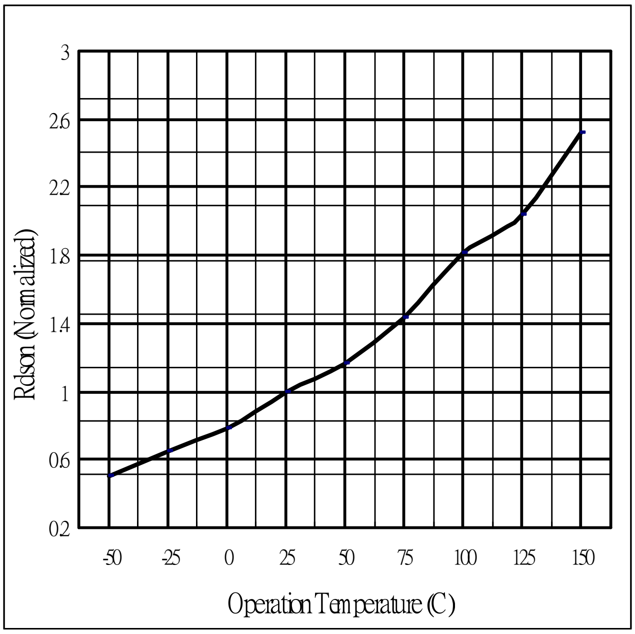


Fig.2 Breakdown Voltage Variation vs. Temperature

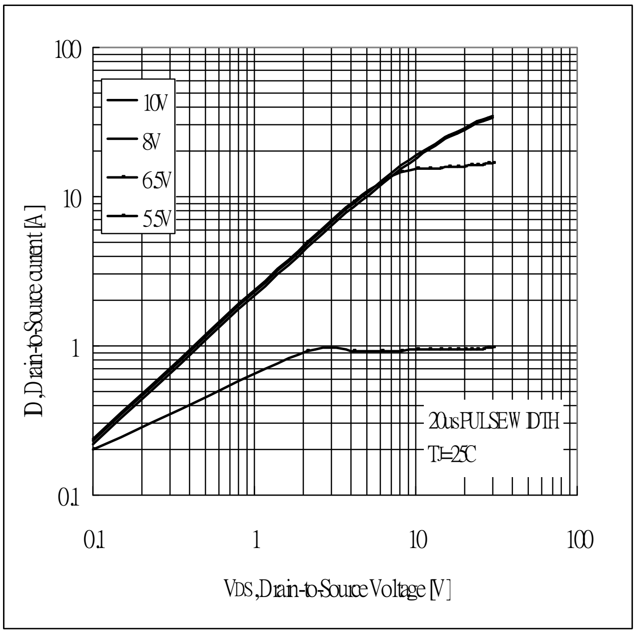


Fig 3. Typical Output Characteristics

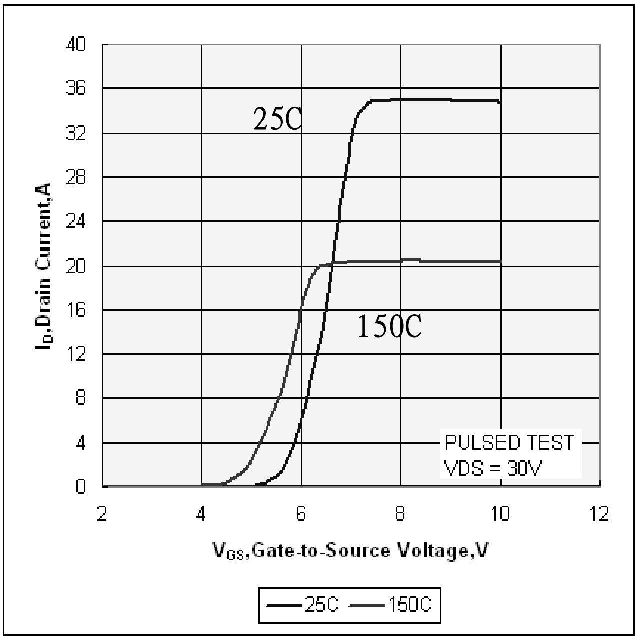


Fig 4. Typical Transfer Characteristics

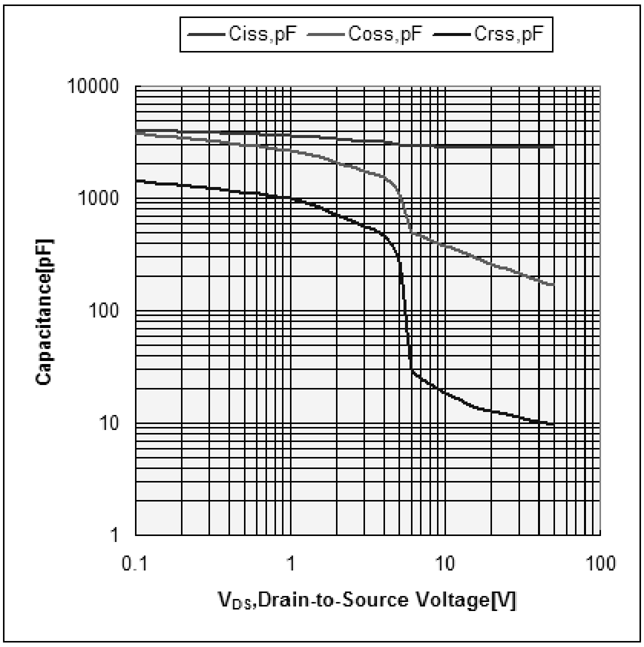


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

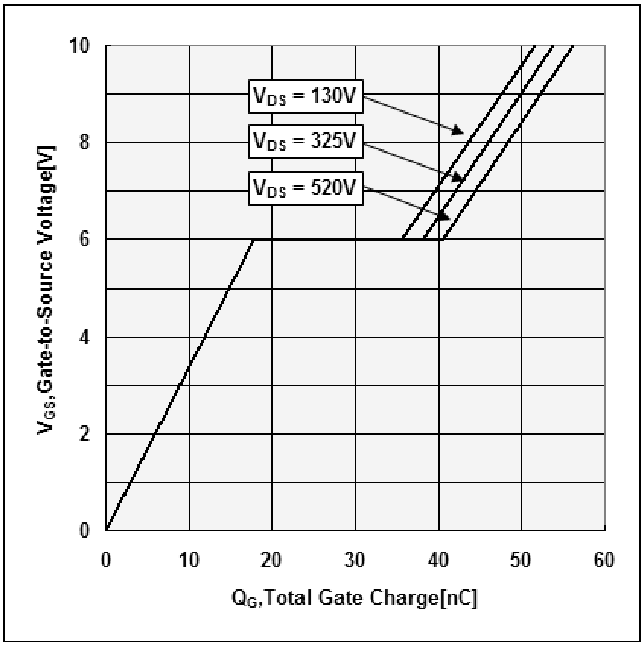
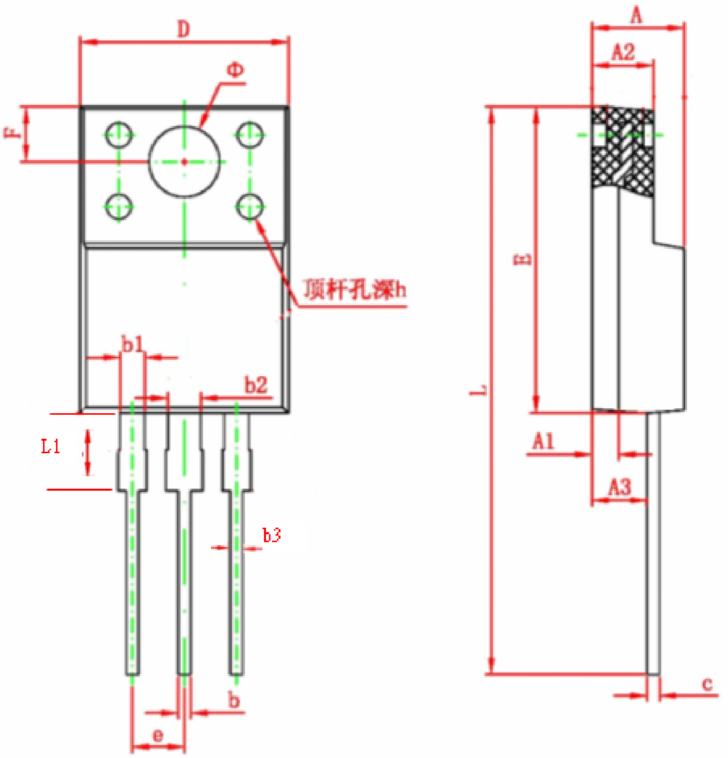


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

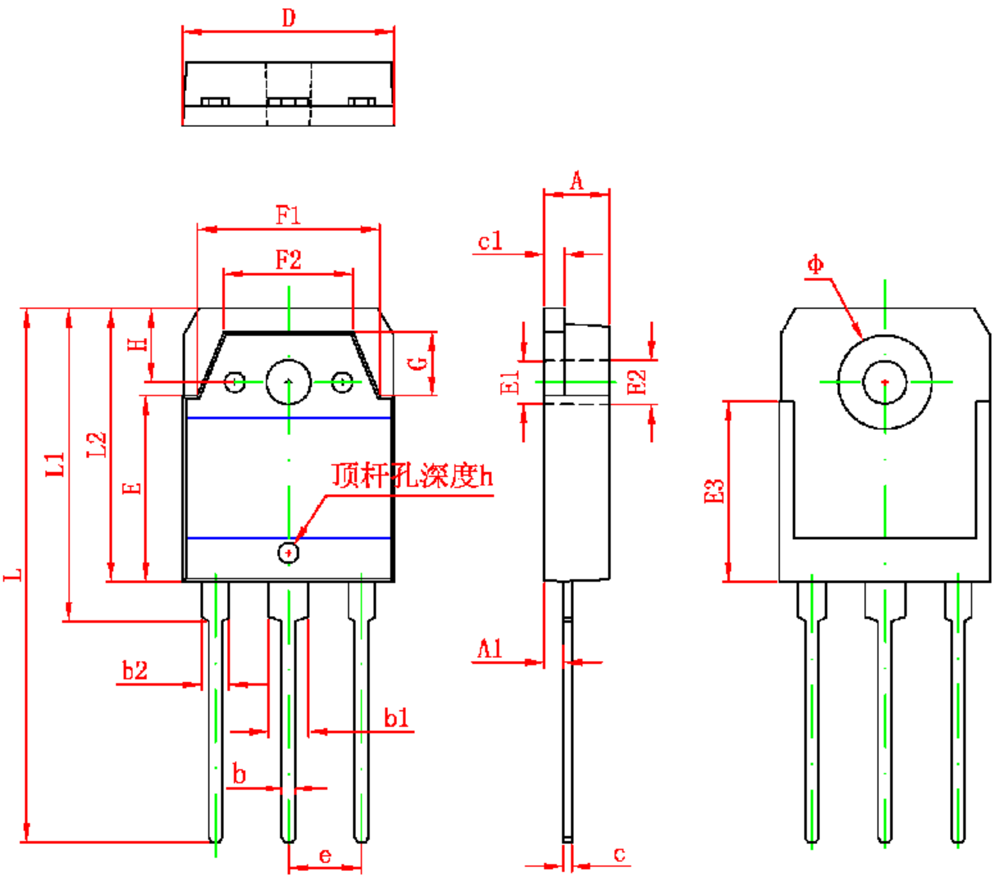
PACKAGE DIMENSION

TO-220F



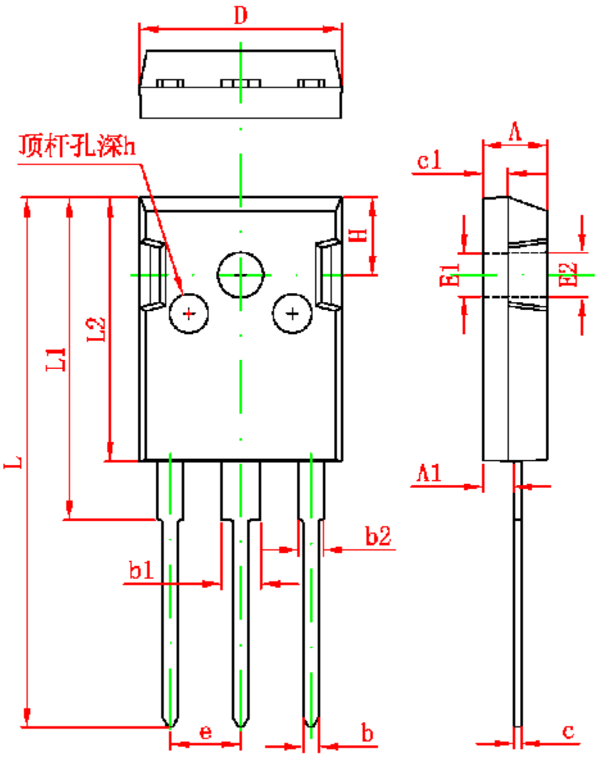
Symbol	Dimensions In Millimeters	
	Min.	Max
A	3.80	4.70
A1	1.3 REF.	
A2	2.20	3.20
A3	2.10	3.20
b	0.30	0.95
b1	1.00	1.75
b2	1.00	1.75
b3	0.50	0.80
c	0.30	0.90
D	9.90	10.40
E	14.60	16.20
e	2.54 TYP.	
F	3.00 REF.	
Φ	3.50 REF.	
h	0.00	0.30
L	28.00	30.00
L1	3.20	3.55

TO-3P



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.600	5.000	0.181	0.197
A1	1.200	1.600	0.047	0.063
b	0.800	1.200	0.031	0.047
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.450	1.650	0.057	0.065
D	15.450	15.850	0.606	0.622
E	13.700	14.100	0.539	0.555
E1	3.200 REF		0.126 REF	
E2	3.300 REF		0.130 REF	
E3	13.450 REF		0.530 REF	
F1	13.400	13.800	0.528	0.543
F2	9.400	9.800	0.370	0.386
L	39.900	40.300	1.571	1.587
L1	23.200	23.600	0.913	0.929
L2	20.300	20.600	0.799	0.811
Φ	6.900	7.100	0.272	0.280
G	5.150	5.550	0.203	0.219
e	5.450 TYP		0.215 TYP	
H	5.000 REF		0.197 REF	
h	0.000	0.300	0.000	0.012

TO-247



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	
h	0.000	0.300	0.000	0.012

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深圳市冠顺微电子股份有限公司
Shenzhen Great Power Co.,Ltd
Web:http:// www.grtpower.com

台湾	深圳
台北县汐止市新台五路一段 96 号 21F	深圳市福田区深南大道 7002 号财富广场 A 座 4V，518040
21F., No. 96, Sec. 1, Sintai 5th Rd., Sijhih City, Taipei County 22102, Taiwan, R.O.C.	4V, Tower A, Fortune Plaza, No. 7002, Shennan Road, Futian District, Shenzhen City, China PC : 518040
TEL: +886-2-2696 3558	TEL: +86-755-83709176
FAX: +886-2-2696 3559	FAX: +86-755-83709276